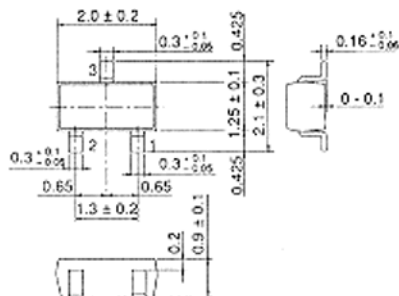


2SC4260

SILICON NPN EPITAXIAL

UHF FREQUENCY CONVERTER, WIDE BAND AMPLIFIER



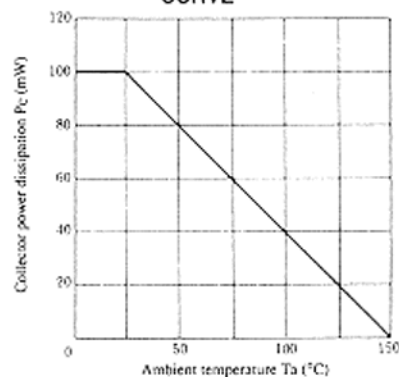
(CMPAK)

1. Emitter
 2. Base
 3. Collector
- (Dimensions in mm)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC4260	Unit
Collector to base voltage	V_{CB0}	25	V
Collector to emitter voltage	V_{CE0}	13	V
Emitter to base voltage	V_{EB0}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	$V_{(BR)CB0}$	$I_C = 10\mu A, I_E = 0$	25	—	—	V
Collector cutoff current	I_{CB0}	$V_{CB} = 15V, I_E = 0$	—	—	0.1	μA
	I_{CE0}	$V_{CE} = 13V, R_{BE} = \infty$	—	—	10	μA
Emitter cutoff current	I_{EB0}	$V_{EB} = 3V, I_C = 0$	—	—	0.3	μA
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 20mA, I_B = 4mA$	—	—	0.3	V
DC current transfer ratio	h_{FE}	$V_{CE} = 5V, I_C = 5mA$	50	—	180	
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	0.85	1.3	pF
Gain bandwidth product	f_T	$V_{CE} = 5V, I_C = 5mA$	3.0	3.8	—	GHz
Conversion gain	CG	$V_{CC} = 5V, I_C = 0.8mA, f = 900MHz$	—	19	—	dB
Noise figure	NF	$f_{osc} = 930MHz(-5dBm), f_{out} = 30MHz$	—	8	—	dB

* Marking is [TT-].

■ See characteristic curves of 2SC4197.